

N-channel 100 V, 0.0145 Ω typ., 45 A, STripFET™ VII DeepGATE™ Power MOSFETs in DPAK, I²PAK and TO-220 packages

Datasheet - production data

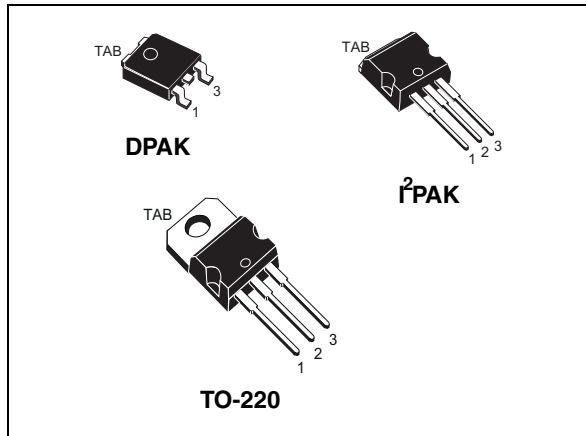
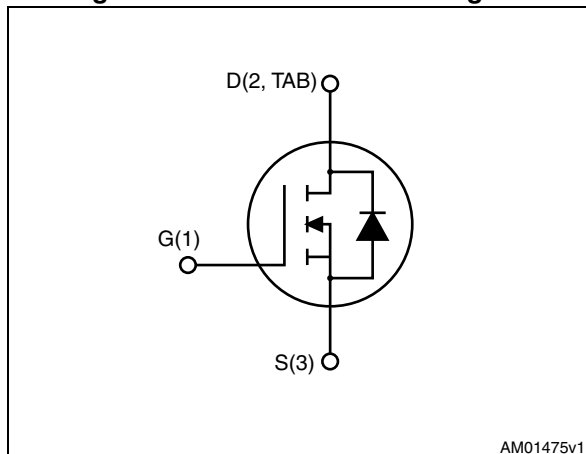


Figure 1. Internal schematic diagram



Features

Order codes	V _{DS}	R _{DS(on)} max. ⁽¹⁾	I _D	P _{TOT}
STD45N10F7	100 V	0.018 Ω	45 A	60 W
STI45N10F7				
STP45N10F7				

1. @ V_{GS} = 10 V

- Ultra low on-resistance
- 100% avalanche tested

Applications

- Switching applications

Description

These devices utilize the 7th generation of design rules of ST's proprietary STripFET™ technology, with a new gate structure. The resulting Power MOSFET exhibits the lowest R_{DS(on)} in all packages.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STD45N10F7	45N10F7	DPAK	Tape and reel
STI45N10F7		I ² PAK	Tube
STP45N10F7		TO-220	

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	100	V
V_{GS}	Gate-source voltage	20	V
I_D	Drain current (continuous) at $T_C = 25\text{ °C}$	45	A
I_D	Drain current (continuous) at $T_C = 100\text{ °C}$	32	A
$I_{DM}^{(1)}$	Drain current (pulsed)	180	A
P_{TOT}	Total dissipation at $T_C = 25\text{ °C}$	60	W
T_J	Operating junction temperature	-55 to 175	°C
T_{stg}	Storage temperature		°C

1. Pulse width limited by safe operating area.

Table 3. Thermal resistance

Symbol	Parameter	Value		Unit
		DPAK	TO-220 I ² PAK	
$R_{thj-case}$	Thermal resistance junction-case	2.5	2.5	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient		62.5	°C/W
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	31.2		°C/W

1. When mounted on FR-4 board of 1inch², 2oz Cu, t < 10 sec.

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ($V_{GS} = 0$)	$I_D = 1\text{ mA}$	100		-	V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 100\text{ V}$			10	μA
		$V_{DS} = 100\text{ V}; T_C = 125\text{ °C}$			100	μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = 20\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.5		4.5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 22.5\text{ A}$		0.0145	0.018	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 50\text{ V}, f = 1\text{ MHz}, V_{GS} = 0$	-	1640	-	pF
C_{oss}	Output capacitance		-	360	-	pF
C_{riss}	Reverse transfer capacitance		-	25	-	pF
Q_g	Total gate charge	$V_{DD} = 50\text{ V}, I_D = 45\text{ A}$	-	25	-	nC
Q_{gs}	Gate-source charge	$V_{GS} = 10\text{ V}$	-	5.1	-	nC
Q_{gd}	Gate-drain charge	Figure 14	-	12.2	-	nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 50\text{ V}, I_D = 22.5\text{ A}, R_G = 4.7\text{ }\Omega, V_{GS} = 10\text{ V}$ Figure 13	-	15	-	ns
t_r	Rise time		-	17	-	ns
$t_{d(off)}$	Turn-off delay time		-	24	-	ns
t_f	Fall time		-	8	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		45	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		180	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 45 \text{ A}$, $V_{GS} = 0$	-		1.1	V
t_{rr}	Reverse recovery time	$I_{SD} = 45 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$, $V_{DD} = 80 \text{ V}$, $T_j = 150 \text{ }^\circ\text{C}$	-	53		ns
Q_{rr}	Reverse recovery charge		-	67		nC
I_{RRM}	Reverse recovery current		-	2.5		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration=300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

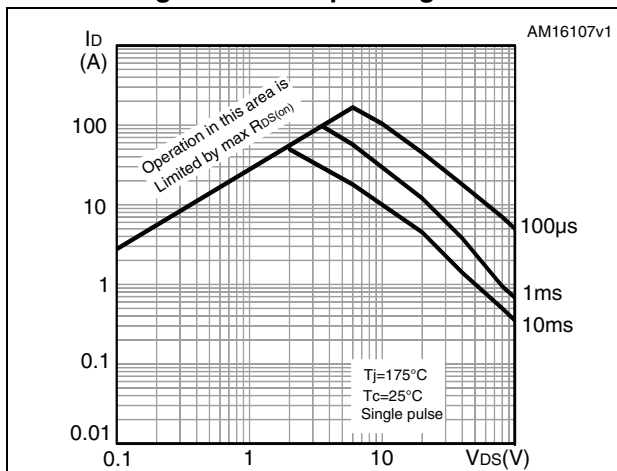


Figure 3. Thermal impedance

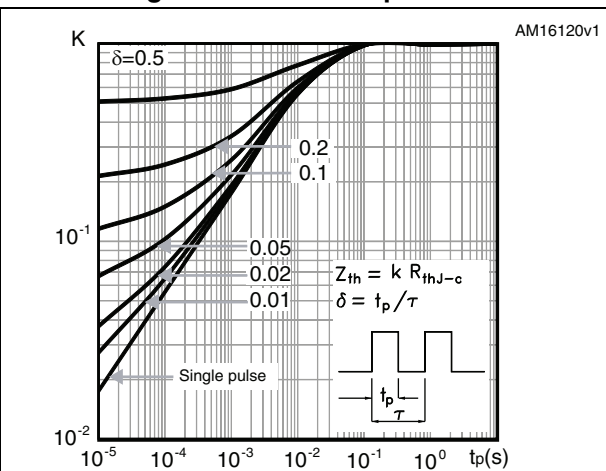


Figure 4. Output characteristics

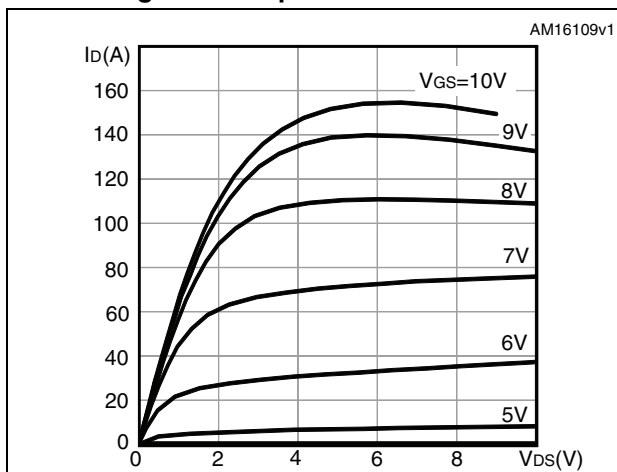


Figure 5. Transfer characteristics

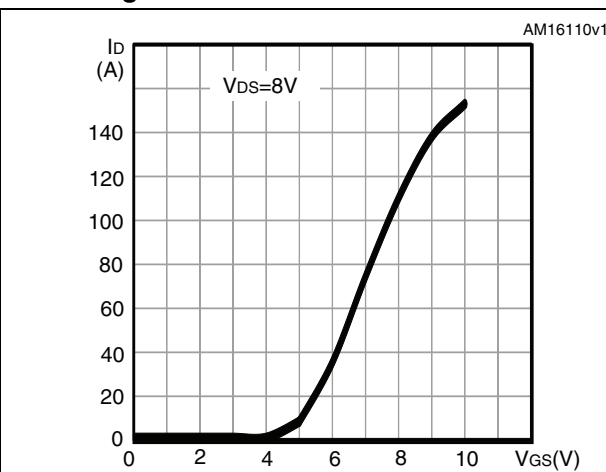


Figure 6. Gate charge vs gate-source voltage

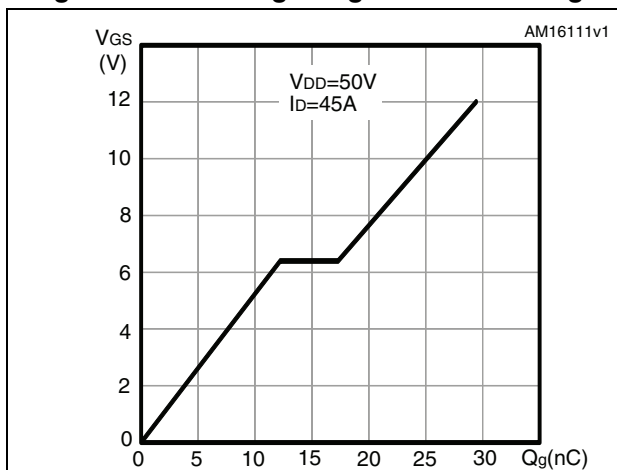


Figure 7. Static drain-source on-resistance

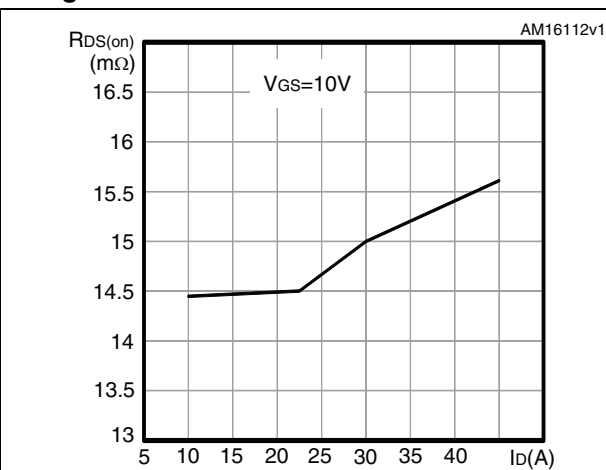


Figure 8. Capacitance variations

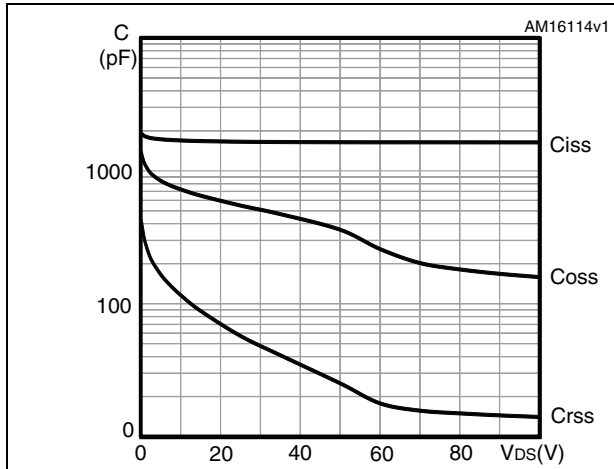


Figure 9. Normalized gate threshold voltage vs temperature

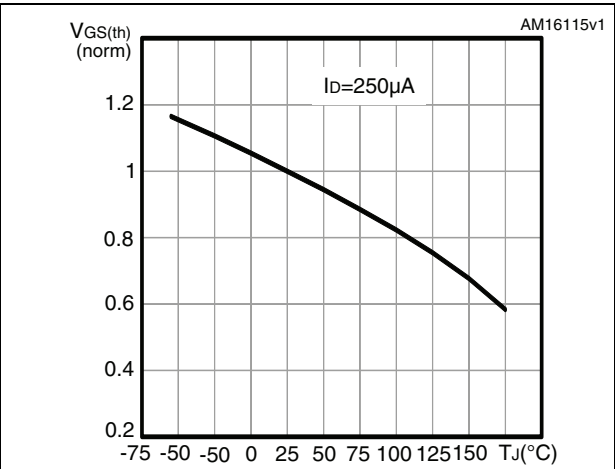


Figure 10. Normalized on-resistance vs temperature

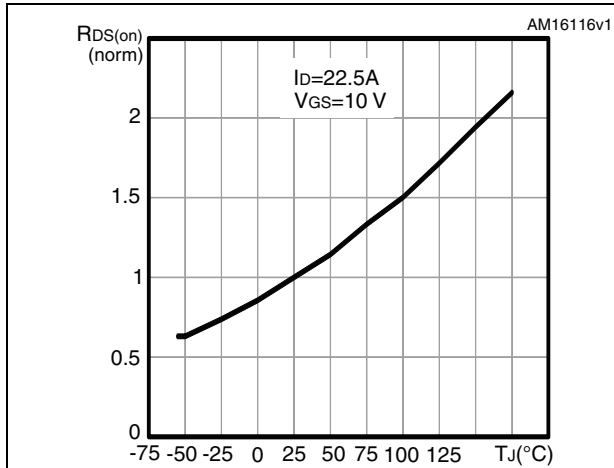


Figure 11. Source-drain diode forward characteristics

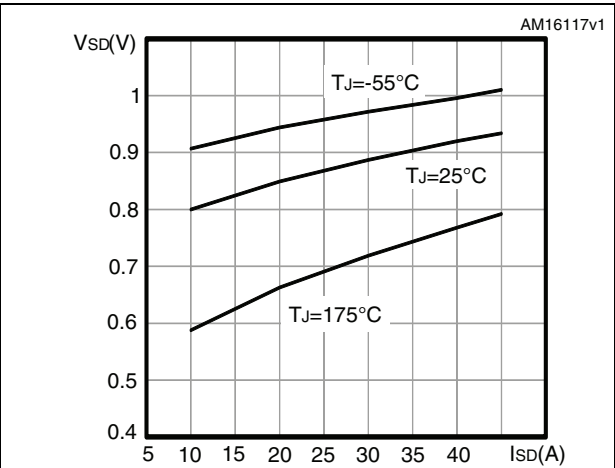
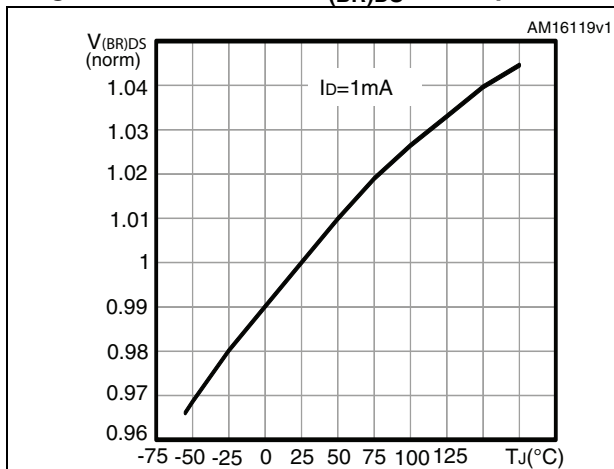


Figure 12. Normalized $V_{(BR)DS}$ vs temperature



3 Test circuits

Figure 13. Switching times test circuit for resistive load

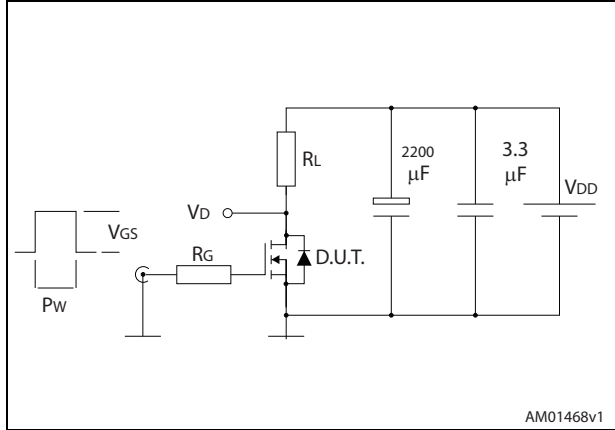


Figure 14. Gate charge test circuit



Figure 15. Test circuit for inductive load switching and diode recovery times

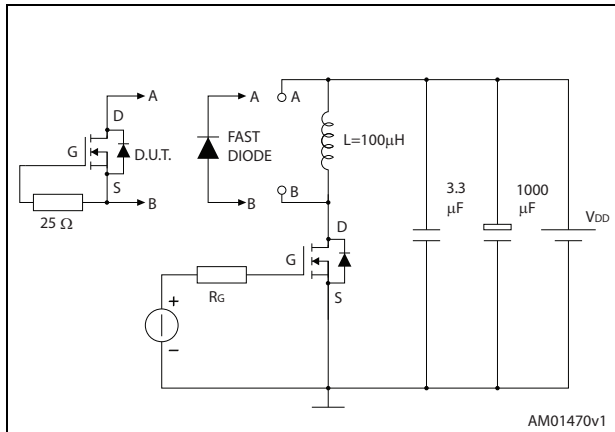


Figure 16. Unclamped inductive load test circuit



Figure 17. Unclamped inductive waveform

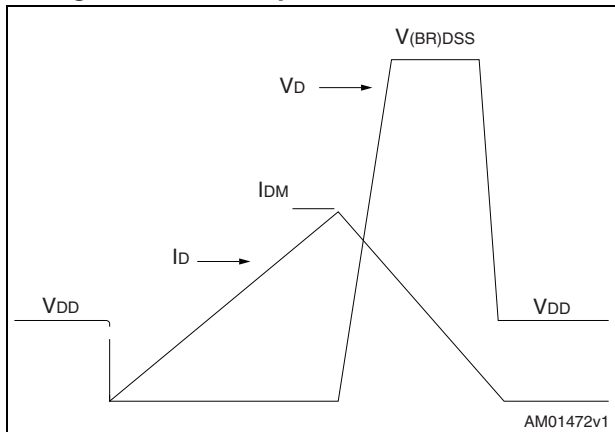
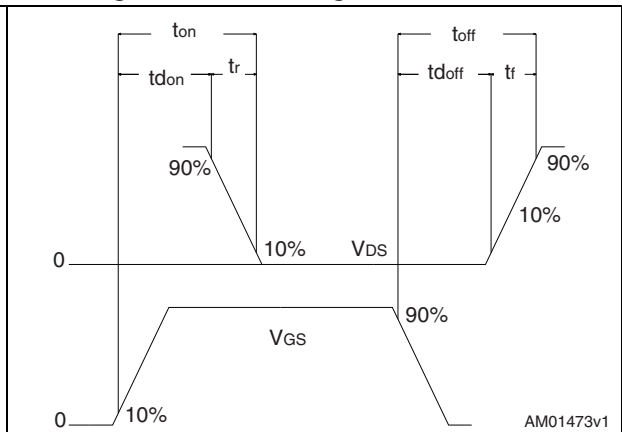


Figure 18. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 8. DPAK (TO-252) type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
(L1)		2.80	
L2		0.80	
L4	0.60		1.00
R		0.20	
V2	0°		8°

Figure 19. DPAK (TO-252) type A drawing

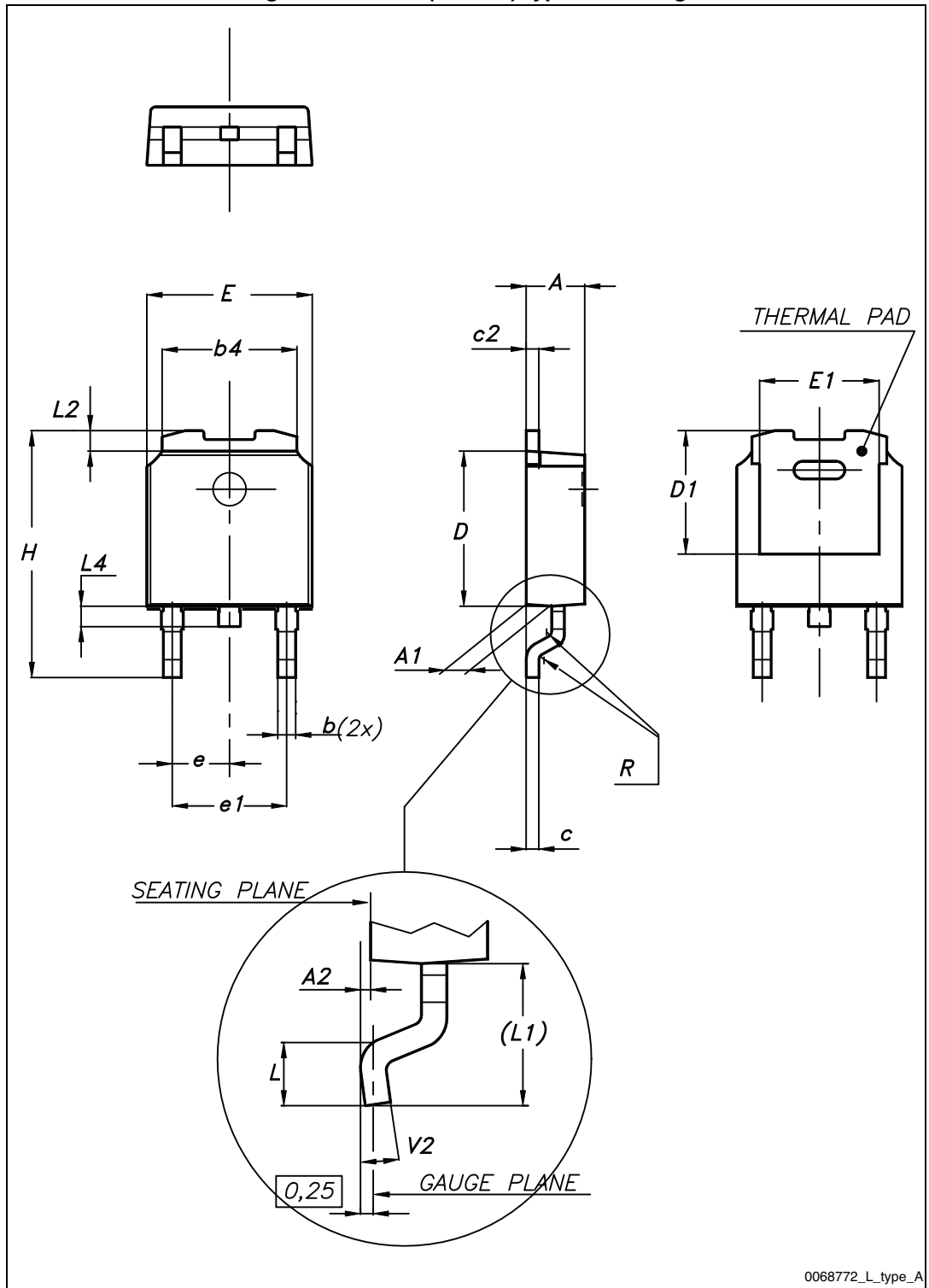
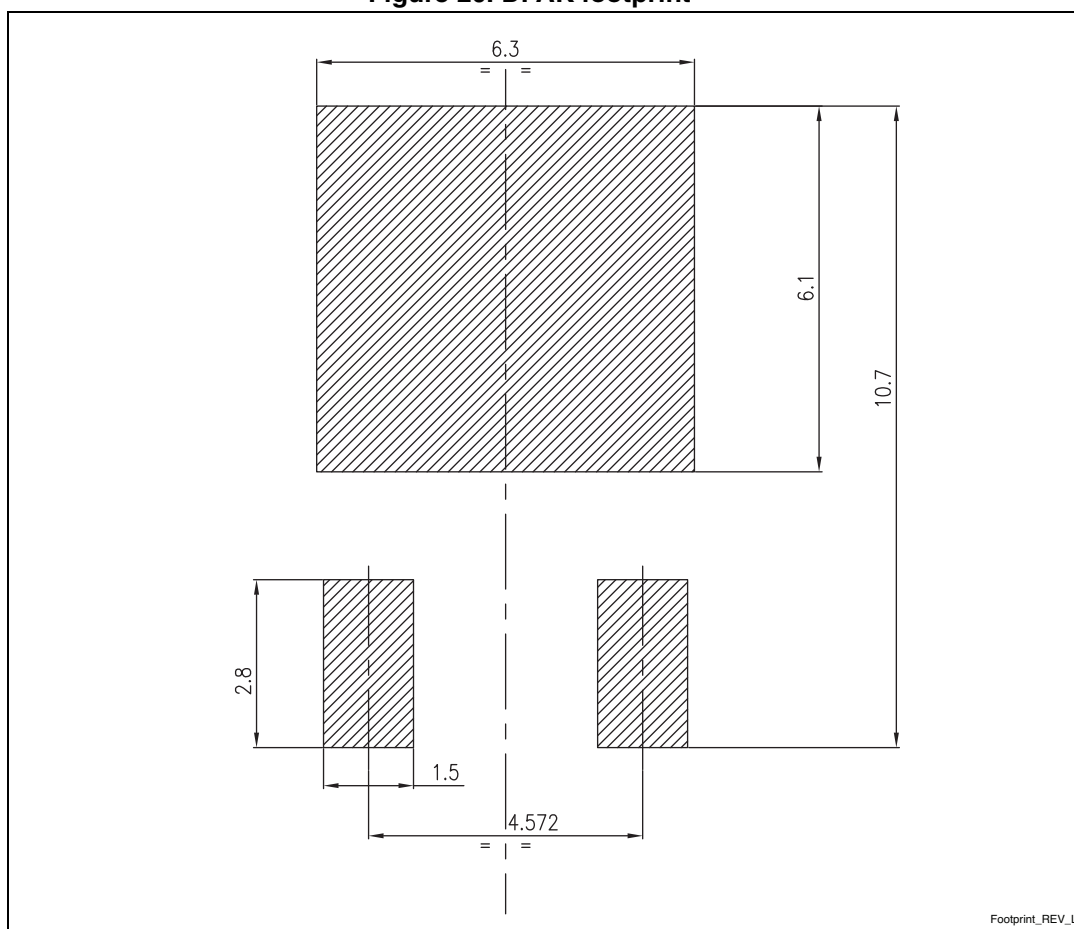


Figure 20. DPAK footprint (a)

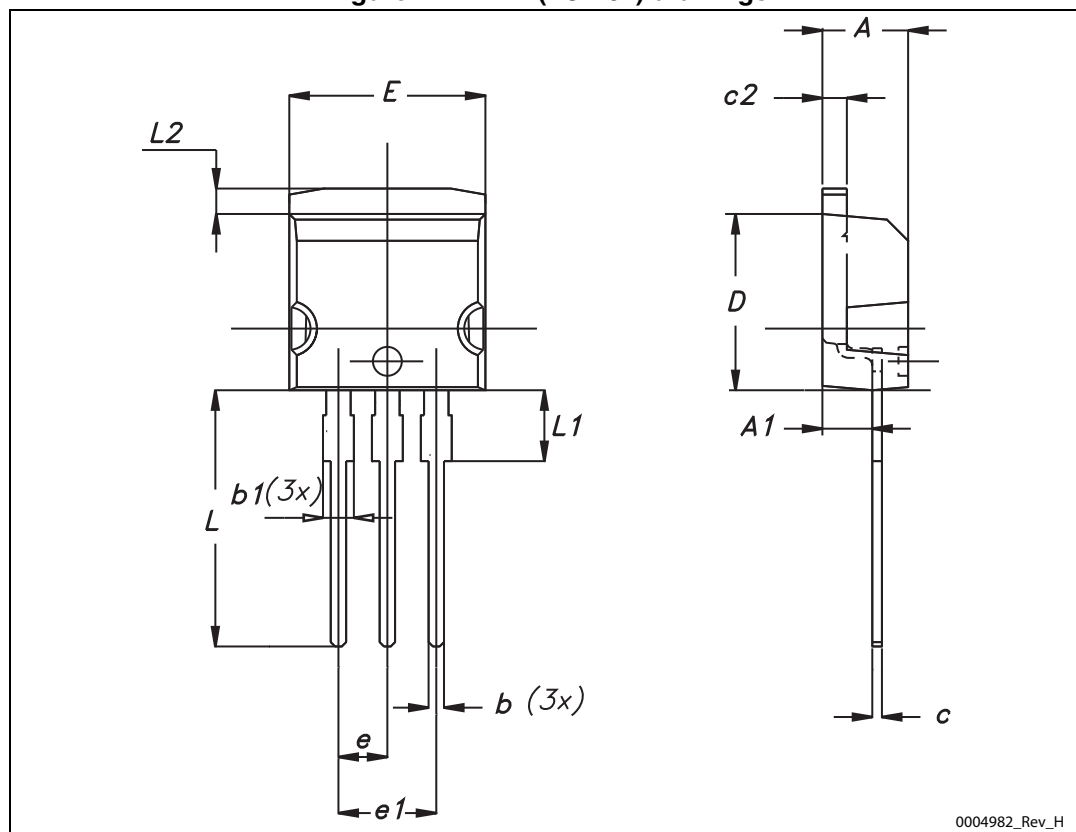


a. All dimensions are in millimeters

Table 9. I²PAK (TO-262) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	2.40		2.72
b	0.61		0.88
b1	1.14		1.70
c	0.49		0.70
c2	1.23		1.32
D	8.95		9.35
e	2.40		2.70
e1	4.95		5.15
E	10		10.40
L	13		14
L1	3.50		3.93
L2	1.27		1.40

Figure 21. I²PAK (TO-262) drawings

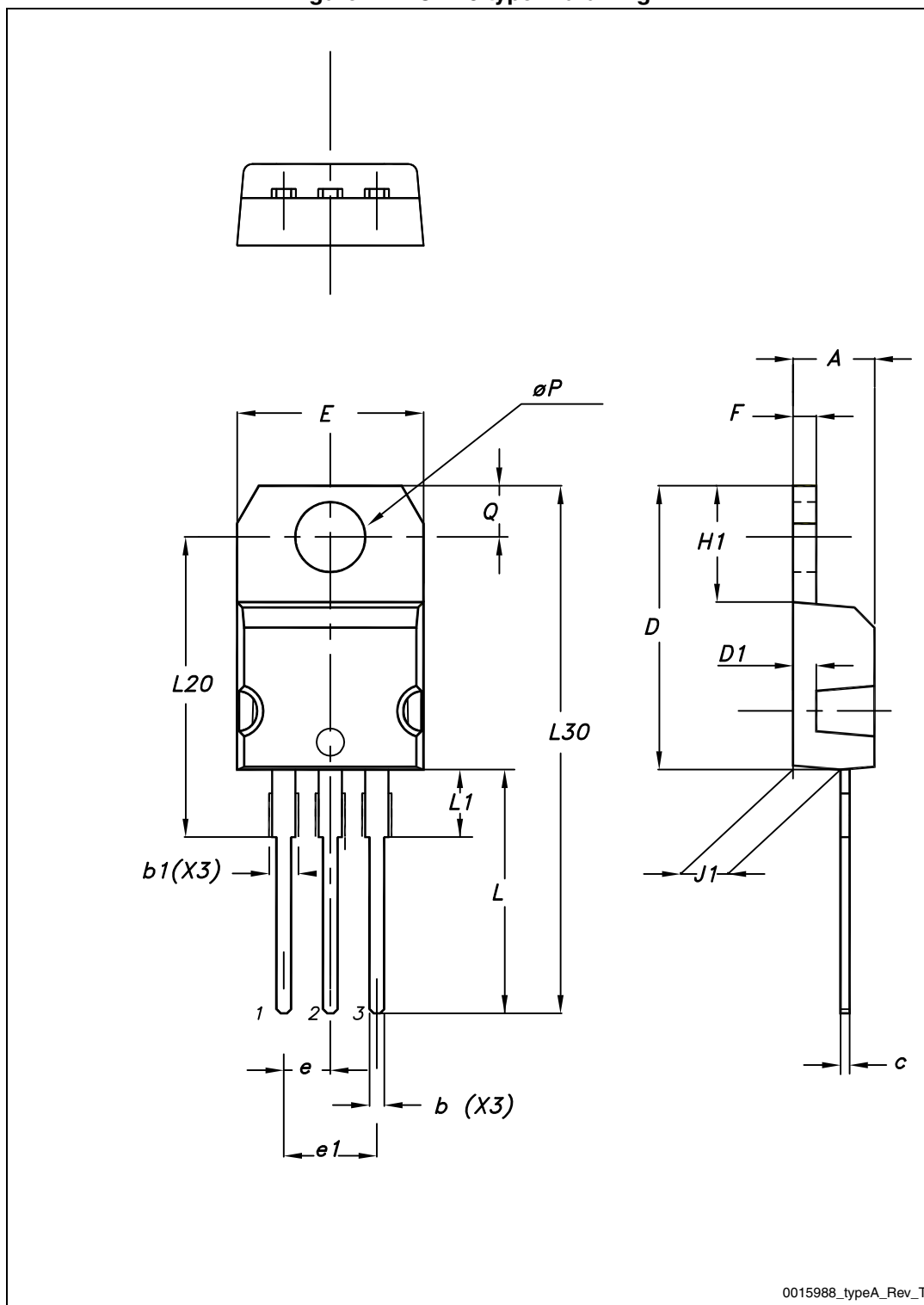


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Table 10. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 22. TO-220 type A drawing



5 Packaging mechanical data

Table 11. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Figure 23. Tape

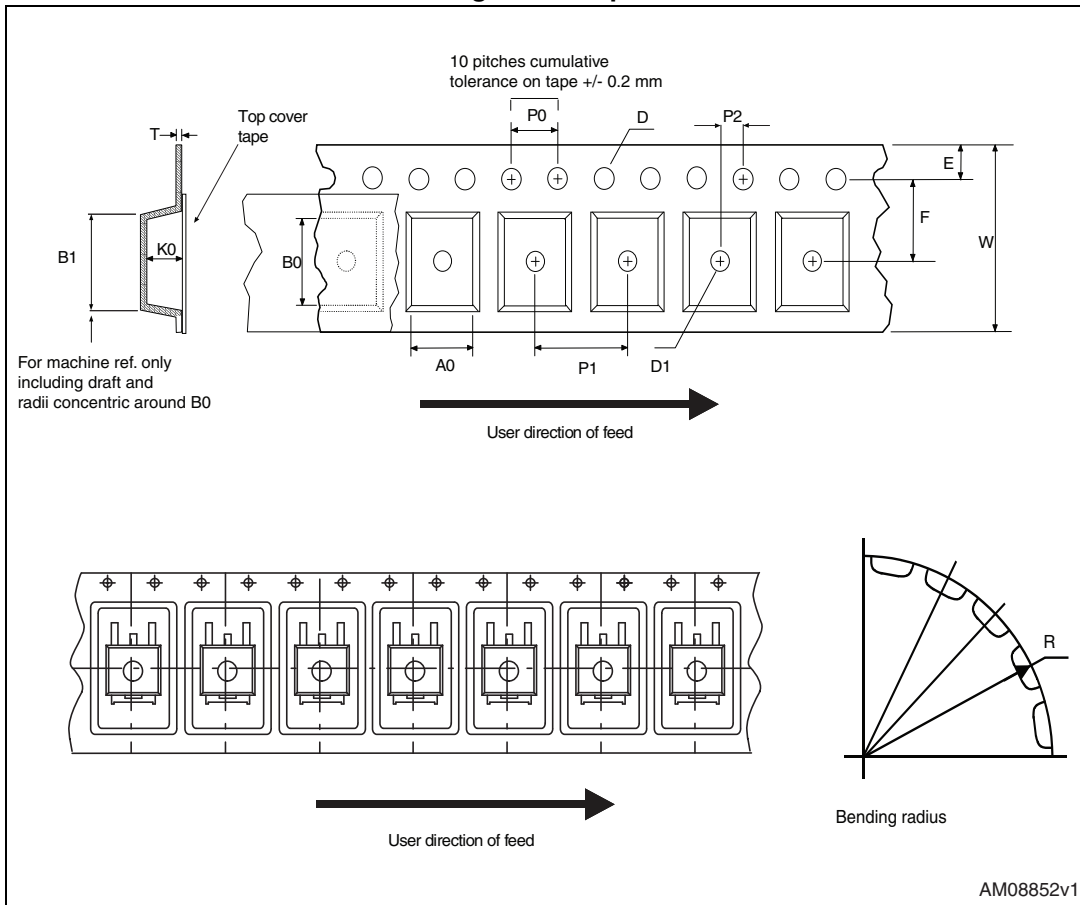
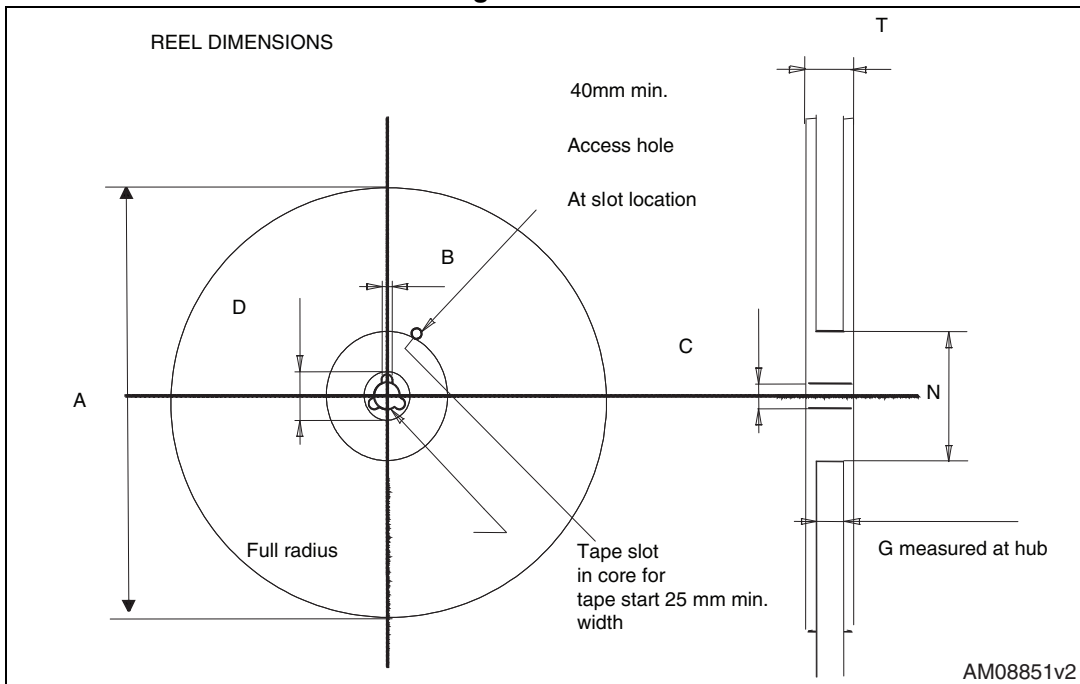


Figure 24. Reel



6 Revision history

Table 12. Document revision history

Date	Revision	Changes
10-Oct-2013	1	First release.

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